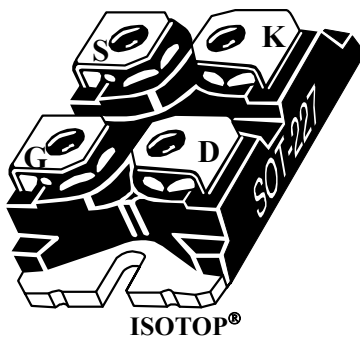
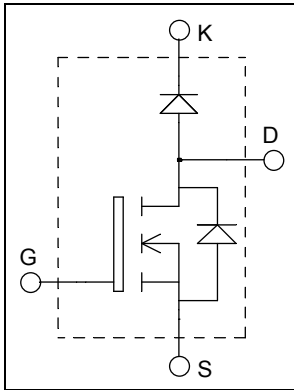


**ISOTOP[®] Boost chopper
MOSFET + SiC chopper diode
Power module**

$V_{DSS} = 500V$
 $R_{DSon} = 65m\Omega$ Max @ $T_j = 25^\circ C$
 $I_D = 58A$ @ $T_c = 25^\circ C$


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- **Power MOS 8TM MOSFET**
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
- **SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	58
		$T_c = 80^\circ C$	43
I_{DM}	Pulsed Drain current	270	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	65	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	543
I_{AR}	Avalanche current (repetitive and non repetitive)	42	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 42\text{A}$			65	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		10800		pF
C_{oss}	Output Capacitance			1164		
C_{riss}	Reverse Transfer Capacitance			148		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 250\text{V}$ $I_D = 42\text{A}$		340		nC
Q_{gs}	Gate – Source Charge			75		
Q_{gd}	Gate – Drain Charge			155		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 333\text{V}$ $I_D = 42\text{A}$ $R_G = 2.2\Omega$		60		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			155		
T_f	Fall Time			50		

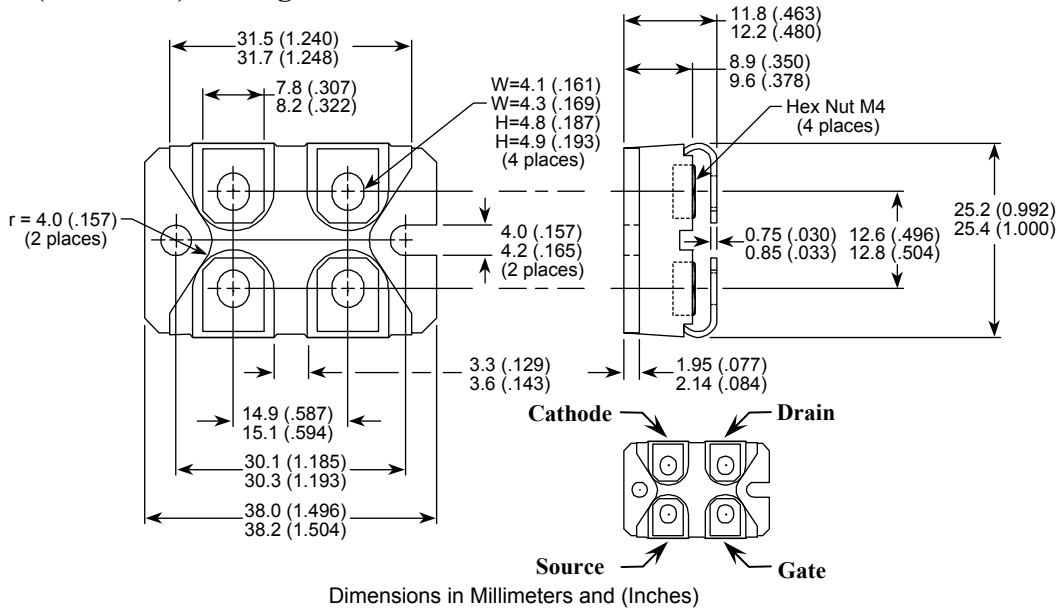
SiC chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$	100	400	μA
			$T_j = 175^\circ\text{C}$	200	2000	
I_F	DC Forward Current			20		A
V_F	Diode Forward Voltage	$I_F = 20\text{A}$	$T_j = 25^\circ\text{C}$	1.6	1.8	V
			$T_j = 175^\circ\text{C}$	2	2.4	
Q_C	Total Capacitive Charge	$I_F = 20\text{A}, V_R = 300\text{V}$ $di/dt = 800\text{A}/\mu\text{s}$		28		nC
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		130		pF
		$f = 1\text{MHz}, V_R = 400\text{V}$		100		

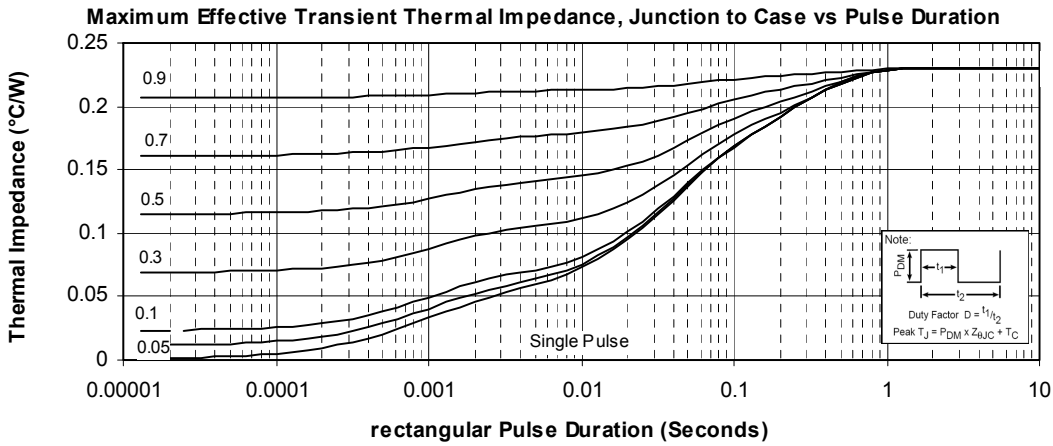
Thermal and package characteristics

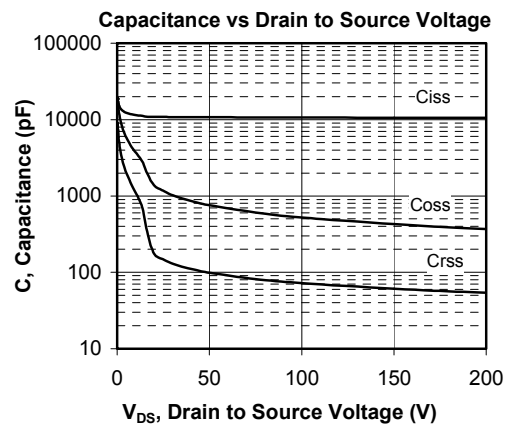
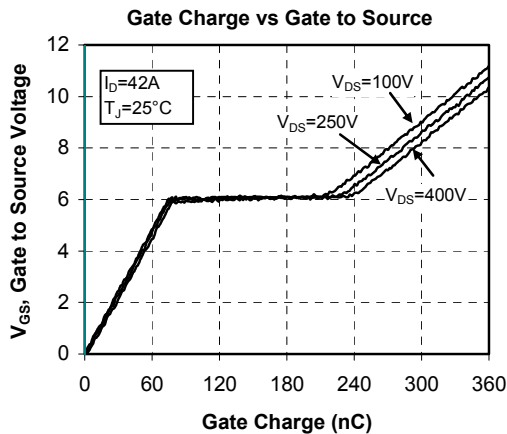
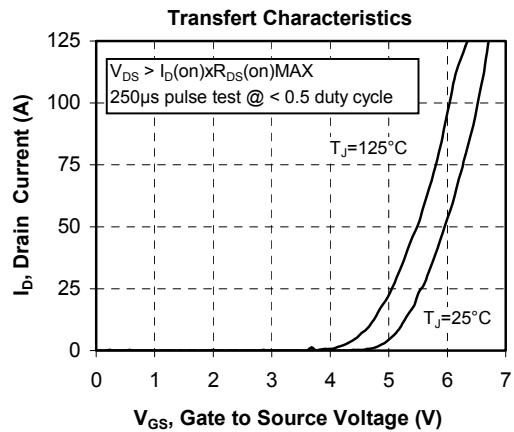
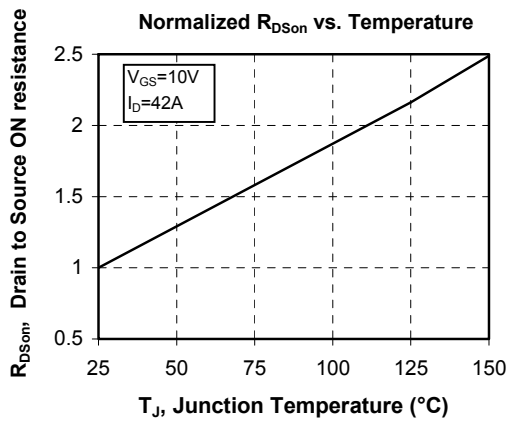
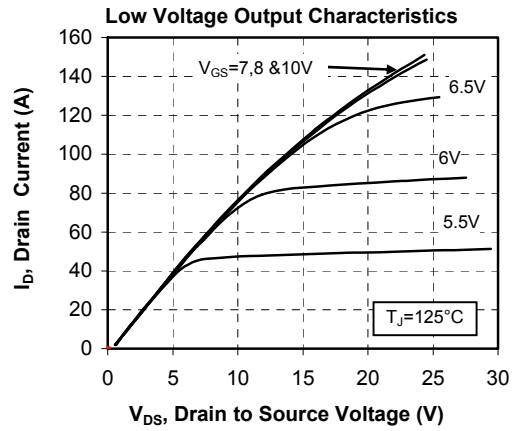
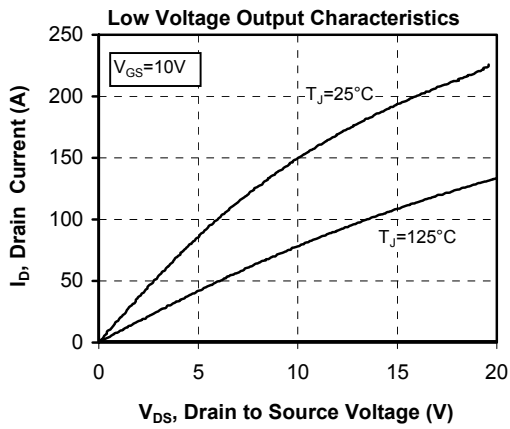
Symbol	Characteristic	Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	Mosfet		0.23	$^\circ\text{C}/\text{W}$
		SiC Diode		1.35	
R_{thJA}	Junction to Ambient (IGBT & Diode)			20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{min}, 50/60\text{Hz}$	2500			V
T_j, T_{STG}	Storage Temperature Range	-40		150	$^\circ\text{C}$
T_L	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

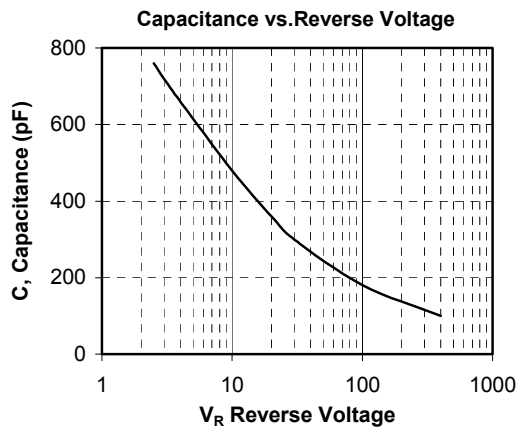
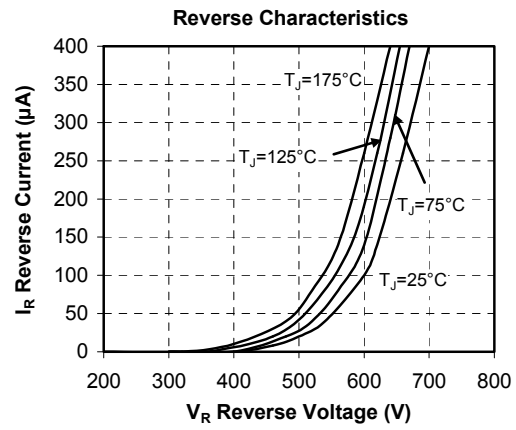
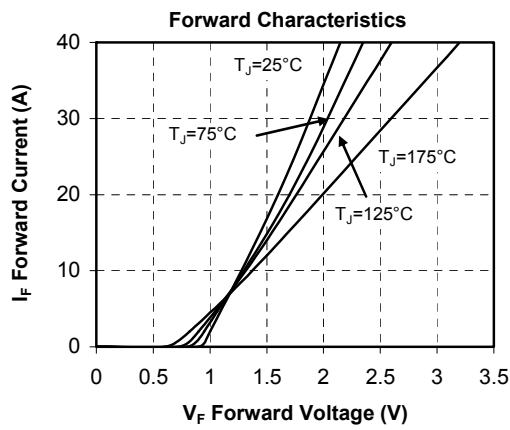
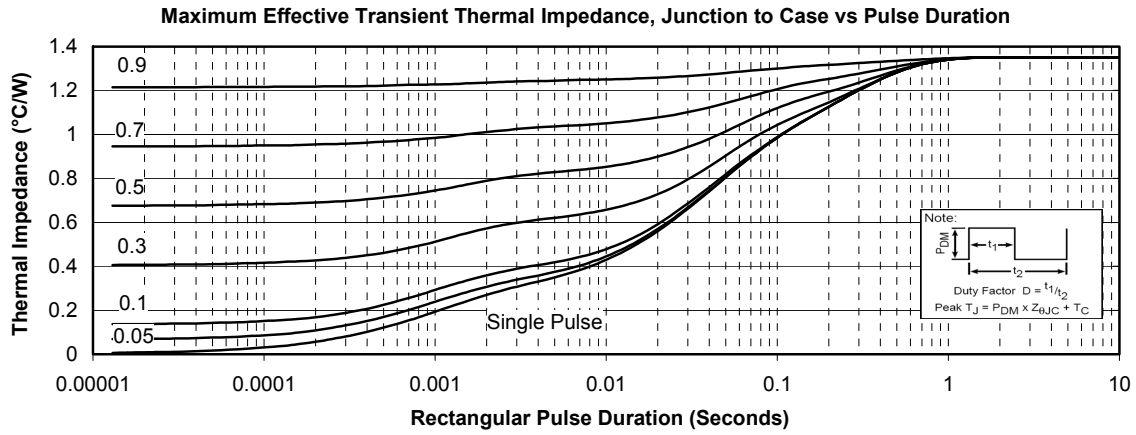
SOT-227 (ISOTOP®) Package Outline



Typical Mosfet Performance Curve





Typical SiC Diode Performance Curve


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